

Kung-Yen Lee

List of Publications by Year in descending order

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37
papers

1,268
citations

687363

13
h-index

454955

30
g-index

37
all docs

37
docs citations

37
times ranked

1295
citing authors

#	ARTICLE	IF	CITATIONS
1	Time Series Analysis Using Composite Multiscale Entropy. Entropy, 2013, 15, 1069-1084.	2.2	262
2	Analysis of complex time series using refined composite multiscale entropy. Physics Letters, Section A: General, Atomic and Solid State Physics, 2014, 378, 1369-1374.	2.1	262
3	Modified multiscale entropy for short-term time series analysis. Physica A: Statistical Mechanics and Its Applications, 2013, 392, 5865-5873.	2.6	164
4	Online Failure Prediction of the Electrolytic Capacitor for LC Filter of Switching-Mode Power Converters. IEEE Transactions on Industrial Electronics, 2008, 55, 400-406.	7.9	118
5	The AC Line Current Regulation Strategy for the Grid-Connected PV System. IEEE Transactions on Power Electronics, 2010, 25, 209-218.	7.9	71
6	Influence of the vertical wind and wind direction on the power output of a small vertical-axis wind turbine installed on the rooftop of a building. Applied Energy, 2018, 209, 383-391.	10.1	62
7	Review of Silicon Carbide Processing for Power MOSFET. Crystals, 2022, 12, 245.	2.2	50
8	An Investigation on Barrier Inhomogeneities of 4H-SiC Schottky Barrier Diodes Induced by Surface Morphology and Traps. IEEE Transactions on Electron Devices, 2012, 59, 694-699.	3.0	33
9	The Correlation of Surface Defects and Reverse Breakdown of 4H-SiC Schottky Barrier Diodes. Journal of Electronic Materials, 2007, 36, 272-276.	2.2	29
10	Low Turn-on voltage dual metal AlGaN/GaN Schottky barrier diode. Solid-State Electronics, 2015, 105, 12-15.	1.4	22
11	Design and Fabrication of 4H-SiC Lateral High-Voltage Devices on a Semi-Insulating Substrate. IEEE Transactions on Electron Devices, 2012, 59, 754-760.	3.0	18
12	Counter-Doped JTE, an Edge Termination for HV SiC Devices With Increased Tolerance to the Surface Charge. IEEE Transactions on Electron Devices, 2015, 62, 354-358.	3.0	18
13	Effect of switching scheme on the performance of a hybrid solar PV system. Renewable Energy, 2016, 96, 520-530.	8.9	16
14	Unveiling the core technology structure for companies through patent information. Technological Forecasting and Social Change, 2010, 77, 1167-1178.	11.6	15
15	Growth and characterization of nitrogen-doped C-face 4H-SiC epilayers. Journal of Crystal Growth, 2006, 297, 265-271.	1.5	14
16	State of charge modeling of lithium-ion batteries using dual exponential functions. Journal of Power Sources, 2016, 315, 331-338.	7.8	13
17	A novel algorithm for single-axis maximum power generation sun trackers. Energy Conversion and Management, 2017, 149, 543-552.	9.2	13
18	Demonstration of CMOS Integration With High-Voltage Double-Implanted MOS in 4H-SiC. IEEE Electron Device Letters, 2021, 42, 78-81.	3.9	12

#	ARTICLE	IF	CITATIONS
19	Influence of ink preparation with the untreated and the burned Pt/C catalysts for proton exchange membrane fuel cells. International Journal of Hydrogen Energy, 2014, 39, 11454-11461.	7.1	10
20	A method for assessing patent similarity using direct and indirect citation links. , 2010, , .		9
21	Influence of the Design of Square p+ Islands on the Characteristics of 4H-SiC JBS. IEEE Transactions on Electron Devices, 2017, 64, 1394-1398.	3.0	8
22	The Impact of Solvents on the Performances of Solution-Processed Indium Gallium Zinc Oxide Thin-Film Transistors Using Nitrate Ligands. Advanced Engineering Materials, 2020, 22, 1901053.	3.5	8
23	1100 V, 22.9 m ² /cm ² 4H-SiC RESURF Lateral Double-Implanted MOSFET With Trench Isolation. IEEE Transactions on Electron Devices, 2021, 68, 5009-5013.	3.0	8
24	3510-v 390-m ² * cm ² 4h-sic lateral jfet on a semi-insulating substrate. IEEE Electron Device Letters, 2009, 30, 957-959.	3.9	7
25	A simplified analog control circuit of a maximum power point tracker. Conference Record of the IEEE Photovoltaic Specialists Conference, 2008, , .	0.0	6
26	A Novel Deep Junction Edge Termination for Superjunction MOSFETs. IEEE Electron Device Letters, 2018, 39, 544-547.	3.9	5
27	Investigation of 3.3 kV 4H-SiC DC-FSJ MOSFET Structures. Micromachines, 2021, 12, 756.	2.9	4
28	The impact of surface morphology on C- and Si-face 4H-SiC Schottky barrier diodes. Physica B: Condensed Matter, 2007, 401-402, 41-43.	2.7	3
29	Influence of low temperature oxidation and nitrogen passivation on the MOS interface of C-face 4H-SiC. Applied Surface Science, 2013, 282, 126-132.	6.1	3
30	Development of solar home system with dual energy storage. SN Applied Sciences, 2019, 1, 1.	2.9	3
31	A balanced pulse-modulated polar transmitter for improved efficiency and stability using power recycling. Microwave and Optical Technology Letters, 2014, 56, 1452-1454.	1.4	1
32	The Design of Quasi-Super Junction and Novel Edge Termination in Junction Barrier Schottky Diode. , 2019, , .		1
33	Correlation of the growth rate for selective epitaxial growth of silicon and oxide thickness and oxide coverage in a reduced pressure chemical vapor deposition pancake reactor. Journal of Vacuum Science & Technology B, 2008, 26, 1712.	1.3	0
34	High voltage lateral 4H-SiC JFETs on a semi-insulating substrate. , 2009, , .		0
35	Characterization for N- and P-type 3C-SiC on Si (100) substrate with thermal anneal and pulsed excimer laser anneal. Applied Surface Science, 2013, 266, 46-50.	6.1	0
36	Feature extraction for bearing fault diagnosis using composite multiscale entropy. , 2013, , .		0

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37	A Novel Design of P Implanted Regions for a Power MOSFET. , 2018, , .		0